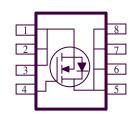
N-Channel 100-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)} m(\Omega)$	I _D (A)		
100	$78 @ V_{GS} = 10V$	5.2		
	92 @ $V_{GS} = 4.5V$	4.8		

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			100	V		
Gate-Source Voltage			±20	·		
	$T_A=25^{\circ}C$] T	±5.2			
Continuous Drain Current ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1D	±3.9	Α		
Pulsed Drain Current ^b			±50			
Continuous Source Current (Diode Conduction) ^a		I_S	2.3	A		
D	$T_A=25^{\circ}C$	D	3.1	W		
Power Dissipation ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	Ir D	2.2			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Maximum	Units	
Maximum Junction-to-Case ^a	t <= 5 sec	$R_{ heta JC}$	25	°C/W	
Maximum Junction-to-Ambient ^a	t <= 5 sec	$R_{ heta JA}$	50	°C/W	

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

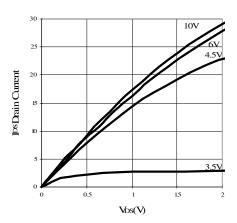
SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)							
Donomoton	Cryssk al	Tark Care 124 area	Limits			T I 24	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static	-				-	-	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	$I_{ m DSS}$	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Dram Current	-DSS	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			A	
Drain-Source On-Resistance ^A	r _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 5.2 \text{ A}$			78	mO	
Drain-Source On-Resistance		$V_{GS} = 4.5 \text{ V}, I_D = 4.8 \text{ A}$			92	mΩ	
Forward Tranconductance ^A	${f g}_{ m fs}$	$V_{DS} = 15 \text{ V}, I_D = 5.2 \text{ A}$		40		S	
Diode Forward Voltage	V_{SD}	$I_S = 2.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.7		V	
Dynamic ^b							
Total Gate Charge	Q_{g}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_{D} = 5.2 \text{ A}$		12.5		nC	
Gate-Source Charge	Q_{gs}			2.6			
Gate-Drain Charge	$Q_{ m gd}$			4.6			
Switching							
Turn-On Delay Time	$t_{d(on)}$			20			
Rise Time	t _r	$V_{DD} = 25 \text{ V}, R_L = 25 \Omega$, $I_D = 1 \text{ A}$,		9		nS	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}$		70		113	
Fall-Time	t_{f}			20			

Notes

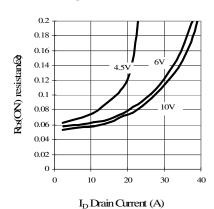
- a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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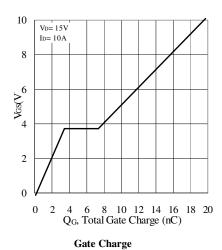
Typical Electrical Characteristics

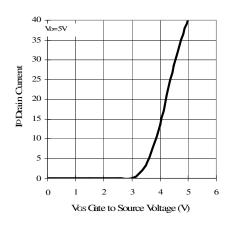


Output Characteristics

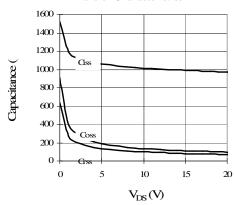


On-Resistance vs. Drain Current

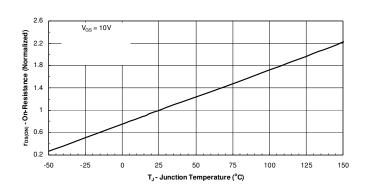




Transfer Characteristics

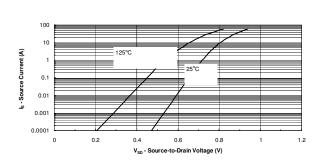


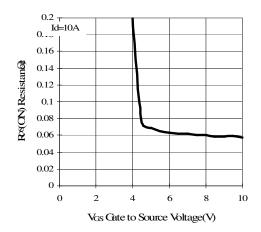
Capacitance



On-Resistance vs. Junction Temperature

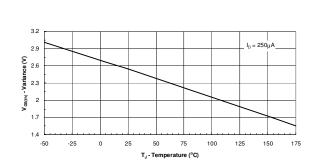
Typical Electrical Characteristics

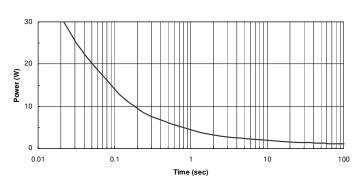


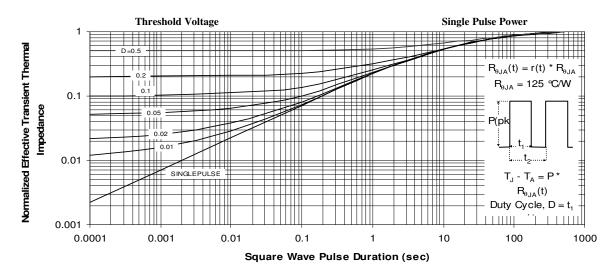


Source-Drain Diode Forward Voltage

On-Resistance vs.Gate-to Source Voltage



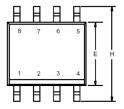


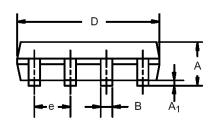


Normalized Thermal Transient Impedance, Junction-to-Ambient

Package Information

SO-8: 8LEAD





	MILLIM	IETERS	INC	HES
Dim	Min	Max	Min	Max
Α	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
В	0.35	0.51	0.014	0.020
С	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
е	1.27 BSC		0.050 BSC	
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°

